



512Mb NAND FLASH

AFND1216U1



512Mbit (32Mx16Bit) NAND FLASH

Revision No.	History	Draft Date	Remark
Rev.00	Initial Draft	Jan. 2011	Preliminary
Rev.01	<ul style="list-style-type: none">- . Adjust operating temperature- . Adjust AC characteristic items<ol style="list-style-type: none">1. Output Load : CL= 100pF → 50pF2. tRC = 42ns → 30ns3. tREA = 30ns → 18ns4. tCEA = 35ns → 30ns	Feb. 2011	



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FEATURES SUMMARY

- **Power Supply**

- 3.3V Device(AFND1216U1) 2.7V ~ 3.6V

- **Organization**

- Memory Cell Array : (32M + 1M) x 16bits

- Data Register : (256 + 8) x 16bits

- **Automatic Program and Erase**

- Page Program : (256 + 8) x 16bits

- Block Erase : (8K +256)Words = 32pages

- **Page Read Operation**

- Page Size : (256 + 8)Words

- Random Access : 15us(Max.)

- Serial Page Access : 30ns(Min.)

- **Fast Write Cycle Time**

- Program time : 200us(Typ.)

- Block Erase time : 2ms(Typ.)

- **Copy-Back PROGRAM Operation**

- Fast Page copy without external buffering

- **Command Register Operation**

- **Security features**

- OTP area, 8KWords(32 pages)

- **Hardware Data Protection**

- Program / Erase locked during Power transitions

- **Data Integrity**

- Endurance : 100K Program / Erase Cycles
(With 1bit/264Words ECC)

- Data Retention : 10 years

- **Package**

- AFND1216U1 : Pb-Free Package

- 48-pin TSOP(12 x 20 / 0.5 mm pitch)

- 48-Ball FBGA: 9.0 x 9.0 x 1.0mm



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GENERAL DESCRIPTION

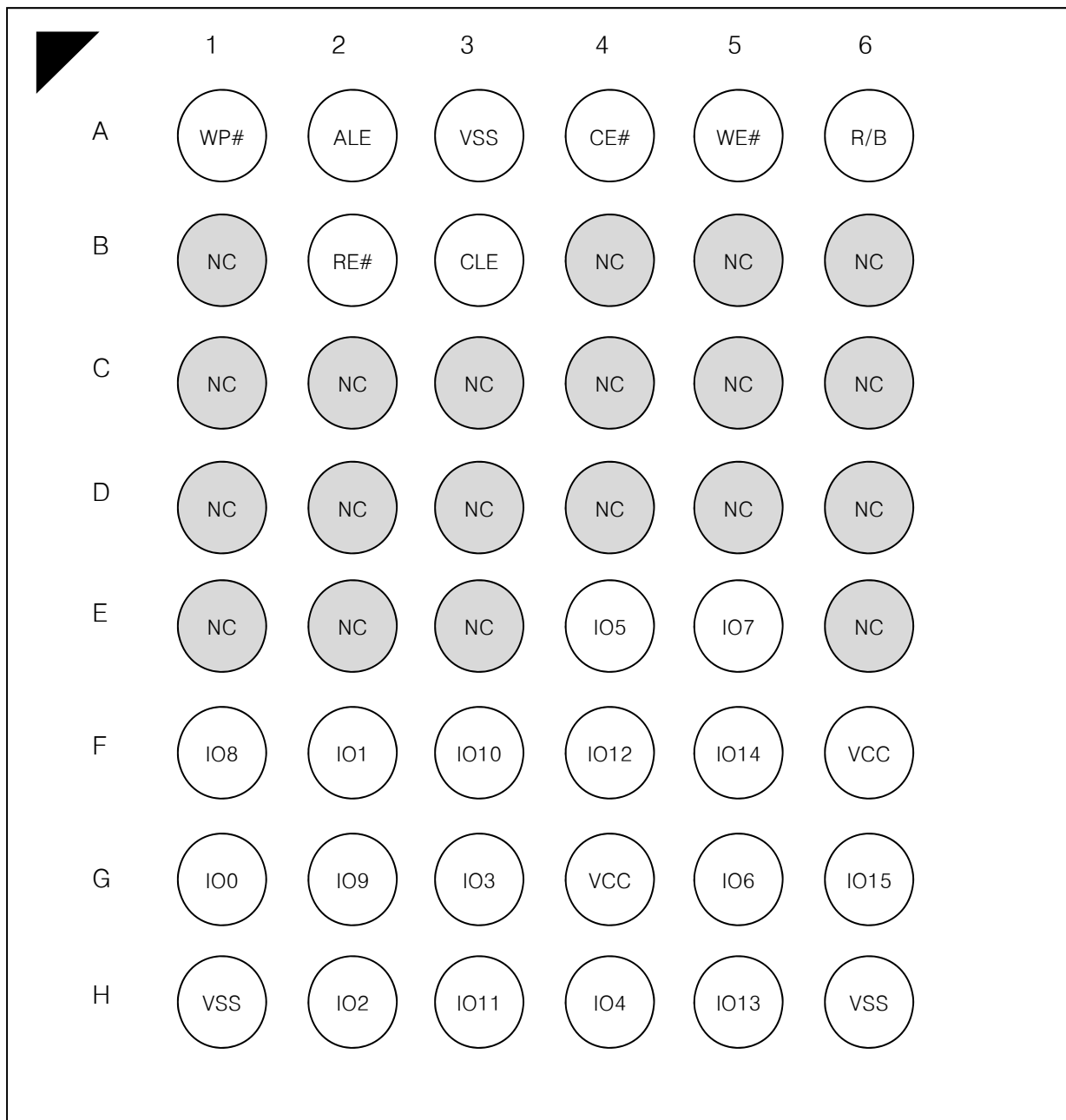
The AFND1216U1 is 512Mbit with spare 16Mbit capacity. The device is offered in 3.3V power supply. Its NAND cell provides the most cost-effective solution for the solid state mass storage market. The memory is divided into blocks that can be erased independently so it possible to preserve valid data while old data is erased. The device contains 4096 blocks, composed by 32 pages consisting in two NAND structures of 16 series connected Flash Cells. A program operation can be performed in typical 200us on the 264-words and an erase operation can be performed in typical 2ms on a 8K-words block. Data in the page can be read out at 30ns cycle time per byte. The I/O pins serve as the ports for address and data input/output as well as command input. Command, Data and Address are synchronously introduced using /CE, /WE, ALE and CLE input pin. The output pin R/B(open drain buffer) signals the status of the device during each operation. In a system with multiple memories the R/B pins can be connected all together to provide a global status signal. The on-chip write control automates all program and erase functions including pulse repetition, where required, and internal verification and margining of data. Even the write-intensive systems can take advantage of the AFND1216U1's extended reliability of 100K program / erase cycles by providing ECC(Error Correction Code) with real time mapping-out algorithm.

The chip could be offered with the /CE don't care function. This function allows the direct download of the code form the NAND flash memory device by a microcontroller, since the /CE transitions do not stop the read operation.

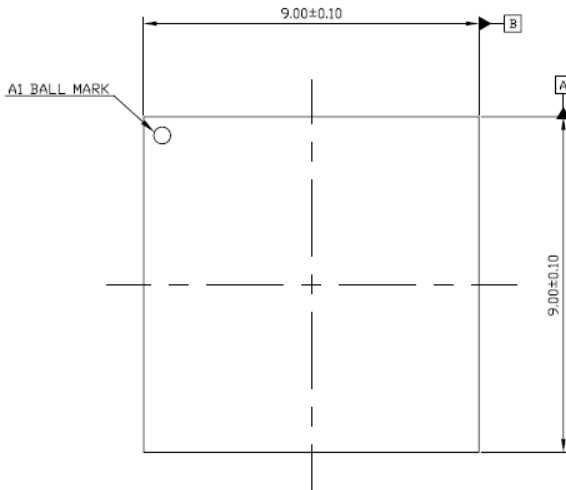
The copy back function allows the optimization of defective blocks management : when a page program operation fails the data can be directly programmed in another page inside the same array section without the time consuming serial data insertion phase. Also, this device includes extra features like OTP area, Block mechanism, Automatic Read at power up, Read ID2 extension.

The AFND1216U1 is an optimum solution for large nonvolatile storage applications such as solid state file storage and other portable applications requiring non-volatility.

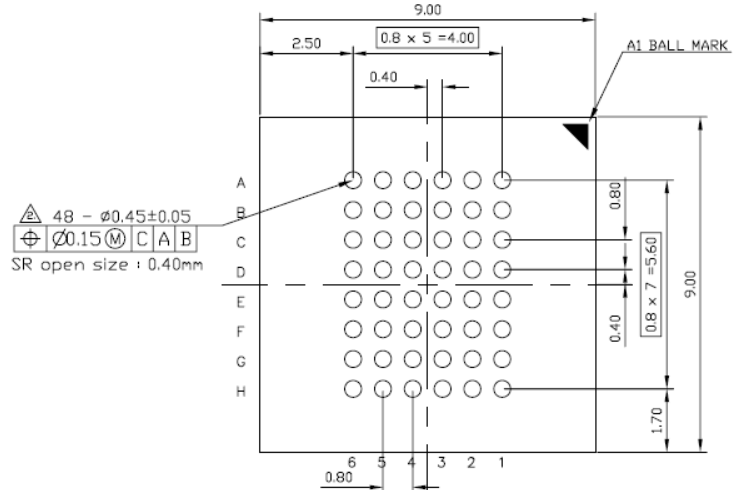
PIN CONFIGURATION (48ball-FBGA)



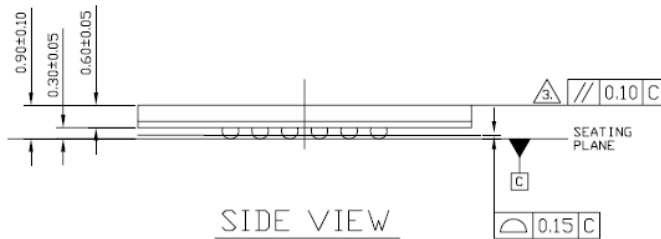
PACKAGE OUTLINE DRAWING (48ball-FBGA 9x9mm)



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Description
FBGA 48BALL
Dimension
9.0mm x 9.0mm x 0.90mm (Max. 1.0mm T)

1. ALL DIMENSIONS are in Millimeters.
2. POST REFLOW SOLDER BALL DIAMETER.
(Pre Reflow diameter : $\varnothing 0.40 \pm 0.02$)

PIN DESCRIPTION

Pin Name	Pin Function
I/O0 ~ I/O15	DATA INPUTS/OUTPUTS The I/O pins are used to input command, address and data, and to output data during read operations. The I/O pins float to high-z when the chip is deselected or when the outputs are disabled.
CLE	COMMAND LATCH ENABLE The CLE input controls the activating path for commands sent to the command register. When active high, commands are latched into the command register through the I/O ports on the rising edge of the /WE signal.
ALE	ADDRESS LATCH ENABLE The ALE input controls the activating path for address to the internal address registers. Addresses are latched on the rising edge of /WE with ALE high
/CE	CHIP ENABLE The /CE input is the device selection control. When the device is in the Busy state, /CE high is ignored, and the device does not return to standby mode in program or erase operation. Regarding /CE control during read operation, refer to 'Page Read' section of device operation.
/RE	READ ENABLE The /RE input is the serial data-out control, and when active drives the data onto the I/O bus. Data is valid tREA after the falling edge of /RE which also increments the internal column address counter by one.
/WE	WRITE ENABLE The /WE input controls writes to the I/O port. Commands, address and data are latched on the rising edge of the /WE pulse.
/WP	WRITE PROTECT The /WP pin provides inadvertent write/erase protection during power transitions. The internal high voltage generator is reset when the /WP pin is active low.
R/B	READY/BUSY OUTPUT The R/B output indicates the status of the device operation. When low, it indicates that a program, erase or random read operation is in process and returns to high state upon completion. It is an open drain output and does not float to high-z condition when the chip is deselected or when outputs are disabled.
VCC	POWER VCC is the power supply for device.
VSS	GROUND
N.C	NO CONNECTION Lead is not internally connected.

Note : Connect all Vcc and Vss pins of each device to common power supply outputs
Do not leave Vcc or Vss disconnected.

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Figure 1. AFND1216U1 FUNCTIONAL BLOCK DIAGRAM

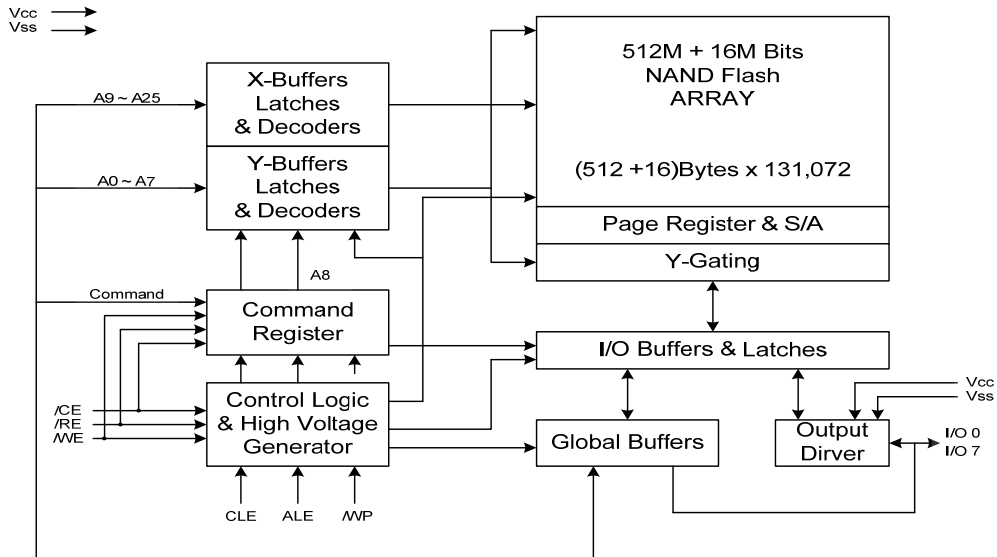
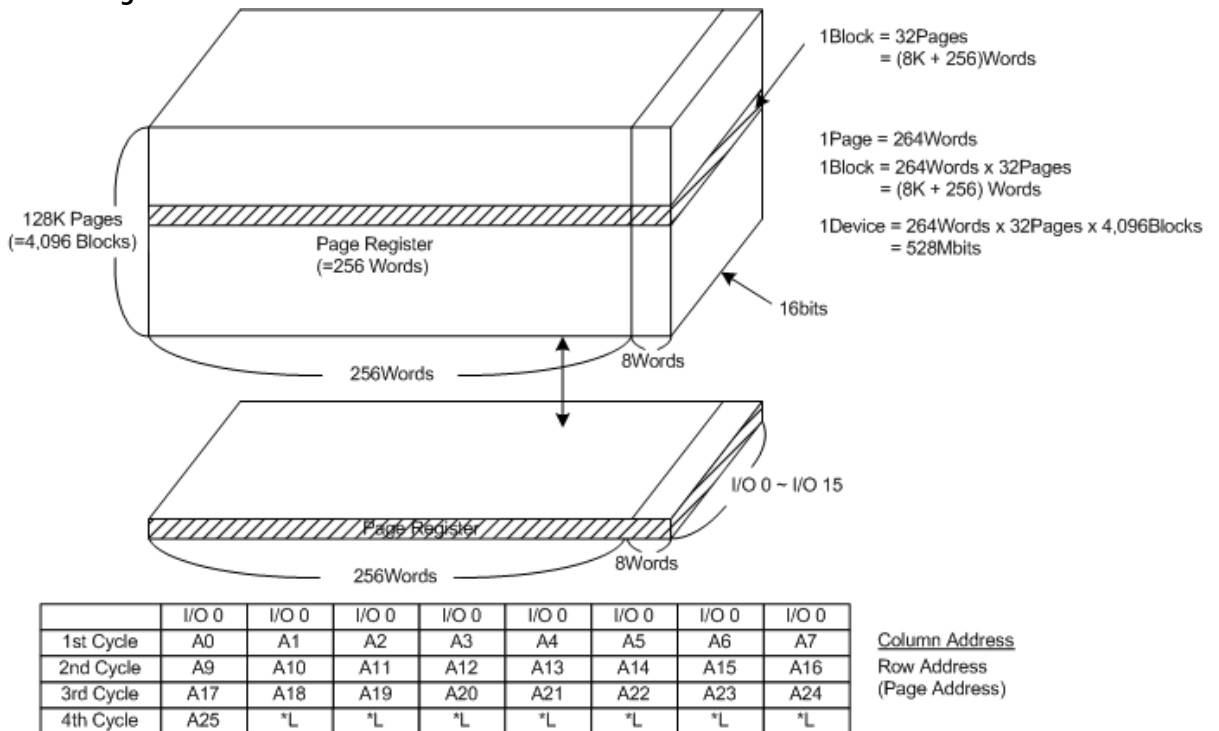


Figure 2. AFND1216U1 ARRAY ORGANIZATION



NOTE : The device ignores any additional input of address cycles than required.
I/O8-I/O15 must be set to Low.